

TÃ¼lay serin

List of Publications by Year in descending order

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papers

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citations

471371

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37
all docs

37
docs citations

37
times ranked

1259
citing authors

#	ARTICLE	IF	CITATIONS
1	Annealing effects on the properties of copper oxide thin films prepared by chemical deposition. <i>Semiconductor Science and Technology</i> , 2005, 20, 398-401.	1.0	195
2	The role of the interface insulator layer and interface states on the current-transport mechanism of Schottky diodes in wide temperature range. <i>Microelectronic Engineering</i> , 2006, 83, 499-505.	1.1	105
3	Crossover from Nearest-Neighbor Hopping Conduction to Efrosâ€™Shklovskii Variable-Range Hopping Conduction in Hydrogenated Amorphous Silicon Films. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 111203.	0.8	59
4	The effects of film thickness on the optical properties of TiO_2/SnO_2 compound thin films. <i>Physica Scripta</i> , 2011, 84, 065602.	1.2	52
5	Studies on optical properties of antimony doped SnO_2 films. <i>Applied Surface Science</i> , 2015, 352, 16-22.	3.1	42
6	Monitoring the characteristic properties of Ga-doped ZnO by Raman spectroscopy and atomic scale calculations. <i>Journal of Molecular Structure</i> , 2019, 1180, 505-511.	1.8	40
7	Pirani Vacuum Gauges Using Silicon-on-Glass and Dissolved-Wafer Processes for the Characterization of MEMS Vacuum Packaging. <i>IEEE Sensors Journal</i> , 2009, 9, 263-270.	2.4	39
8	The thickness effect on the electrical conduction mechanism in titanium oxide thin films. <i>Journal of Alloys and Compounds</i> , 2010, 493, 227-232.	2.8	39
9	Electronâ€™Electron Interactions in Sb-Doped SnO_2 Thin Films. <i>Journal of Electronic Materials</i> , 2010, 39, 1152-1158.	1.0	37
10	Hopping conduction in In-doped CuO thin films. <i>Applied Surface Science</i> , 2014, 318, 105-107.	3.1	37
11	Estimation of compensation ratio by identifying the presence of different hopping conduction mechanisms in SnO_2 thin films. <i>Thin Solid Films</i> , 2011, 519, 2302-2307.	0.8	34
12	Multiphonon hopping of carriers in CuO thin films. <i>Physica B: Condensed Matter</i> , 2011, 406, 3551-3555.	1.3	30
13	Extraction of important electrical parameters of CuO. <i>Physica B: Condensed Matter</i> , 2011, 406, 575-578.	1.3	28
14	Comprehensive structural analysis and electrical properties of (Cu, Al and In)-doped SnO_2 thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2019, 251, 114445.	1.7	23
15	An Understanding of the Band Gap Shrinkage in Sn-Doped ZnO for Dye-Sensitized Solar Cells. <i>Journal of Electronic Materials</i> , 2017, 46, 6739-6744.	1.0	22
16	Electrical And Microstructural Properties Of (Cu, Al, In)-doped SnO_2 Films Deposited By Spray Pyrolysis. <i>Advanced Materials Letters</i> , 2014, 5, 309-314.	0.3	21
17	Current-limiting property of Cu/cupric oxide/Cu sandwich structure. <i>Semiconductor Science and Technology</i> , 2002, 17, 60-64.	1.0	18
18	Identification of Current Transport Mechanisms and Temperature Sensing Qualifications for $Al/(ZnS-PVA)/p-Si$ Structures at Low and Moderate Temperatures. <i>IEEE Sensors Journal</i> , 2022, 22, 99-106.	2.4	18

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19	Barrier-controlled electron transport in Sn-doped ZnO polycrystalline thin films. <i>Thin Solid Films</i> , 2012, 522, 90-94.	0.8	16
20	Enhancement of Nonlinear Absorption in Defect Controlled ZnO Polycrystalline Thin Films by Means of Co-Doping. <i>Physica Status Solidi (B): Basic Research</i> , 2021, 258, 2000539.	0.7	15
21	Effects of Co and Cu dopants on the structural, optical, and electrical properties of ZnO nanocrystals. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 6088-6092.	1.1	14
22	The change in the electrical transport mechanism from the grain boundary conduction to the nearest-neighbor hopping conduction in SnO ₂ . <i>Journal of Materials Science: Materials in Electronics</i> , 2011, 22, 872-875.	1.1	13
23	Fluctuating in the hopping rate of CuO thin films with respect to substrate temperature. <i>Superlattices and Microstructures</i> , 2012, 52, 759-764.	1.4	13
24	Electrical Properties of Polycrystalline SnO ₂ Thin Films. <i>Applied Physics Express</i> , 2011, 4, 121101.	1.1	12
25	Determination of the critical carrier concentration for the metal-insulator transition in Ga-doped ZnO. <i>Journal of Materials Science: Materials in Electronics</i> , 2018, 29, 14111-14115.	1.1	12
26	Al and X (Sn, Cu, In) co-doped ZnO nanocrystals. <i>Journal of Materials Science: Materials in Electronics</i> , 2016, 27, 6179-6182.	1.1	11
27	The effect of humidity on electronic conductivity of an Au/CuO/Cu ₂ O/Cu sandwich structure. <i>Semiconductor Science and Technology</i> , 2000, 15, 112-116.	1.0	10
28	Carrier transport in In-doped CuO thin films. <i>Philosophical Magazine</i> , 2013, 93, 3110-3117.	0.7	10
29	Influence of oxygen flow rate in CuO. <i>Applied Surface Science</i> , 2015, 352, 155-157.	3.1	7
30	High quality optoelectronic properties of Sb-doped SnO ₂ by spray pyrolysis with less solution. <i>Materials Research Express</i> , 2019, 6, 086423.	0.8	7
31	Investigation of the structural and optical properties of copper-titanium oxide thin films produced by changing the amount of copper. <i>Thin Solid Films</i> , 2019, 685, 293-298.	0.8	6
32	Comparison of characteristic properties of Al, Ga, and In-doped ZnO thin films formed by sol-gel method. <i>Superlattices and Microstructures</i> , 2021, 159, 107034.	1.4	4
33	Effect of reverse-bias annealing on thermal equilibrium changes in hydrogenated amorphous germanium. <i>Semiconductor Science and Technology</i> , 1999, 14, 1048-1051.	1.0	2
34	Determination of thermal annealing effect in intrinsic a-Si:H film. <i>Journal of Non-Crystalline Solids</i> , 2000, 276, 163-168.	1.5	2
35	Determination of the distribution of electronic states in hydrogenated amorphous germanium by capacitance techniques. <i>Semiconductor Science and Technology</i> , 2004, 19, 270-276.	1.0	2
36	The thermal equilibrium changes on reverse bias annealing in Schottky diodes. <i>Semiconductor Science and Technology</i> , 1997, 12, 1451-1454.	1.0	1

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37	The investigation of an annealing effect on the density of states in a-Si:H film. Semiconductor Science and Technology, 1997, 12, 291-295.	1.0	0